

METHOD TO WRITE/READ MRAM ARRAYS

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Abstract of the Disclosure

10 A method of writing/reading an array of magnetoresistive cells, with each cell in
the array having associated therewith a first current line that generates an easy axis field
and a second orthogonal current line that generates a hard axis field when current is
applied thereto. The method includes initially applying a current to the second
orthogonal current lines in a first direction that generates a hard axis field to switch end
15 domains in all cells in the array to a fixed direction, and selecting a cell in the array for
write/read using a half-select technique including supplying a half-select current to the
first current line associated with the selected cell to generate a half-select easy axis field
and, simultaneously, supplying a half-select current in the first direction to the second
current line associated with the selected cell to generate a half-select hard axis field.

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(Fig. 1 to accompany abstract)